



WBFBP-02C Plastic-Encapsulate Diodes

DK400LED02 SWITCHING DIODE

DESCRIPTION

Silicon Epitaxial Planar

FEATURES

- Small Surface Mounting Type
- High Speed
- High Reliability with High Surge Current Handling Capability

WBFBP-02C

(1.0×0.6×0.5)
unit: mm



APPLICATION

High Speed Switching for Detection

For Portable Equipment:(i.e. Mobile Phone,MP3, MD,CD-ROM, DVD-ROM, Note Book PC, etc.)

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Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Value			Unit
Peak Reverse Voltage	V _{RM}	90			V
DC Reverse Voltage	V _R	80			V
Peak Forward Current	I _{FM}	225			mA
Mean Rectifying Current	I _o	100			mA
Surge Current @t=1s	I _{surge}	500			mA
Power dissipation	P _D	100			mW
Thermal resistance junction to ambient	R _{θJA}	1250			°C/W
Junction Temperature	T _j	150			°C
Storage Temperature	T _{stg}	-55~+150			°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _F			1.2	V	I _F =100mA
Reverse current	I _R			0.1	μA	V _R =80V
Capacitance between terminals	C _T			3.0	pF	V _R =0.5V, f=1MHz
Reverse recovery time	t _{rr}			4	ns	V _R =6V, I _F =10mA, R _L =100Ω